

# FDU3N50NZTU

## N-Channel UniFET II MOSFET

500 V, 2.5 A, 2.5  $\Omega$

UniFET II MOSFET is ON Semiconductor's high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET II MOSFET to withstand over 2 kV HBM surge stress. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.

### Features

- $R_{DS(on)} = 2.1 \Omega$  (Typ.) @  $V_{GS} = 10 \text{ V}$ ,  $I_D = 1.25 \text{ A}$
- Low Gate Charge (Typ. 6.2 nC)
- Low  $C_{rss}$  (Typ. 2.5 pF)
- 100% Avalanche Tested
- Improved dv/dt Capability
- ESD Improved Capability
- These Devices are Pb-Free and are RoHS Compliant

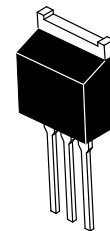
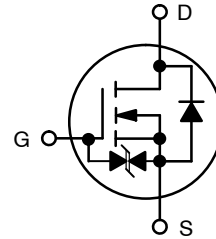
### Applications

- LCD / LED TV
- Lighting
- Charger / Adapter



ON Semiconductor®

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IPAK3  
CASE 369AR

### ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 2 of this data sheet.

# FDU3N50NZTU

## ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>DSS</sub>	Drain-to-Source Voltage	500	V
V <sub>GSS</sub>	Gate-to-Source Voltage	±25	V
I <sub>D</sub>	Drain Current	Continuous (T <sub>C</sub> = 25°C)	2.5
		Continuous (T <sub>C</sub> = 100°C)	1.5
I <sub>DM</sub>	Drain Current	Pulsed (Note 1)	10
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 2)	114	mJ
I <sub>AR</sub>	Avalanche Current (Note 1)	2.5	A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	4	mJ
dv/dt	Peak Diode Recovery (Note 3)	10	V/ns
P <sub>D</sub>	Power Dissipation	T <sub>C</sub> = 25°C	40
		Derate Above 25°C	0.3
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering Purposes (1/8" from case for 5 seconds)	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating; pulse-width limited by maximum junction temperature.
2. L = 36.6 mH, I<sub>AS</sub> = 2.5 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25 Ω, starting T<sub>J</sub> = 25°C.
3. I<sub>SD</sub> ≤ 2.5 A, di/dt ≤ 200 A/s, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C.

## THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case, Max.	3.1	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient, Max.	90	

## PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDU3N50NZTU	FDU3N50NZ	IPAK	Tube	N/A	N/A	75 units

# FDU3N50NZTU

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

$BV_{DSS}$	Drain-to-Source Breakdown Voltage	$I_D = 250 \mu\text{A}$ , $V_{GS} = 0 \text{ V}$ , $T_C = 25^\circ\text{C}$	500	-	-	V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to $25^\circ\text{C}$	-	0.5	-	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 500 \text{ V}$ , $V_{GS} = 0 \text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 400 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $T_C = 125^\circ\text{C}$	-	-	10	
$I_{GSS}$	Gate-to-Body Leakage Current	$V_{GS} = \pm 25 \text{ V}$ , $V_{DS} = 0 \text{ V}$	-	-	$\pm 10$	$\mu\text{A}$

### ON CHARACTERISTICS

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250 \mu\text{A}$	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain-to-Source On Resistance	$V_{GS} = 10 \text{ V}$ , $I_D = 1.25 \text{ A}$	-	2.1	2.5	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 20 \text{ V}$ , $I_D = 1.25 \text{ A}$	-	1.9	-	S

### DYNAMIC CHARACTERISTICS

$C_{iss}$	Input Capacitance	$V_{DS} = 25 \text{ V}$ , $V_{GS} = 0 \text{ V}$ , $f = 1 \text{ MHz}$	-	210	280	$\text{pF}$
$C_{oss}$	Output Capacitance		-	30	45	
$C_{rSS}$	Reverse Transfer Capacitance		-	2.5	5	
$Q_{g(tot)}$	Total Gate Charge at 10 V	$V_{DS} = 400 \text{ V}$ , $I_D = 2.5 \text{ A}$ , $V_{GS} = 10 \text{ V}$ (Note 4)	-	6.2	8	$\text{nC}$
$Q_{gs}$	Gate-to-Source Gate Charge		-	1.4	-	
$Q_{gd}$	Gate-to-Drain "Miller" Charge		-	3.1	-	

### SWITCHING CHARACTERISTICS

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250 \text{ V}$ , $I_D = 2.5 \text{ A}$ , $V_{GS} = 10 \text{ V}$ , $R_G = 25 \Omega$ (Note 4)	-	10	30	ns
$t_r$	Turn-On Rise Time		-	15	40	
$t_{d(off)}$	Turn-Off Delay Time		-	26	60	
$t_f$	Turn-Off Fall Time		-	17	45	

### DRAIN-SOURCE DIODE CHARACTERISTICS

$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	2.5	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	10	
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}$ , $I_{SD} = 2.5 \text{ A}$	-	-	1.4	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0 \text{ V}$ , $I_{SD} = 2.5 \text{ A}$ , $dI_F/dt = 100 \text{ A}/\mu\text{s}$	-	190	-	ns
$Q_{rr}$	Reverse Recovery Charge		-	0.52	-	$\mu\text{C}$

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL CHARACTERISTICS

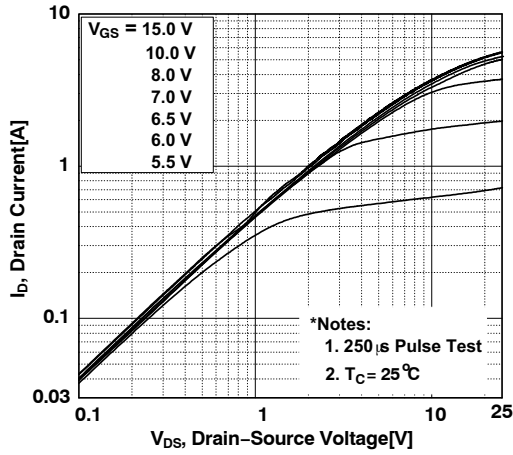


Figure 1. On-Region Characteristics

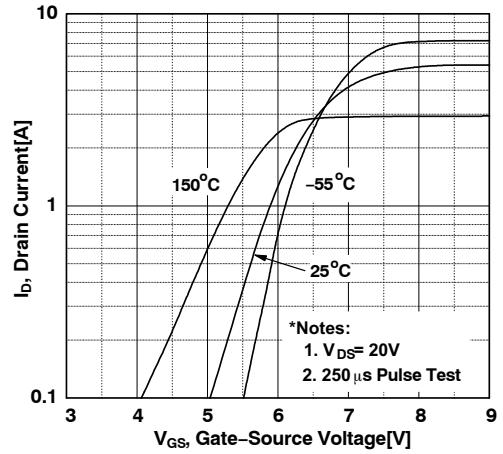


Figure 2. Transfer Characteristics

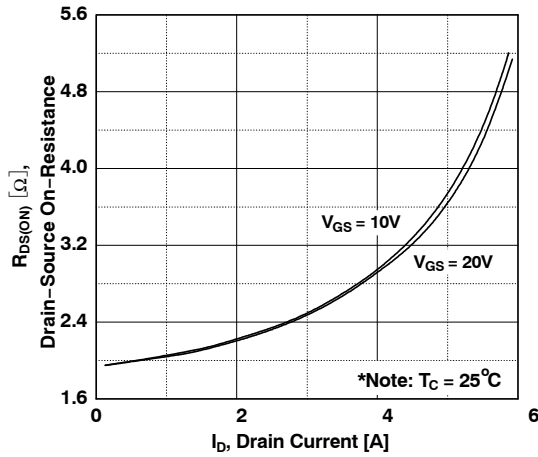


Figure 3. On-Resistance vs. Gate-to-Source Voltage

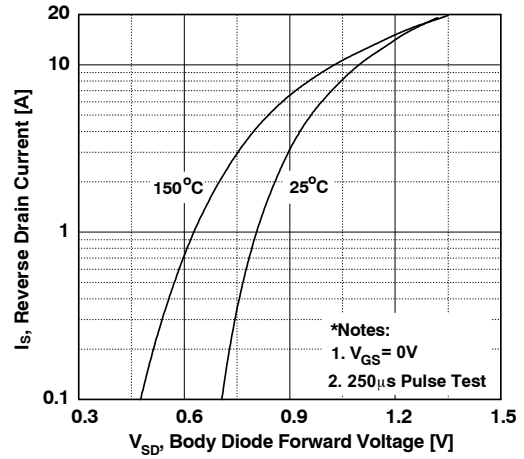


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

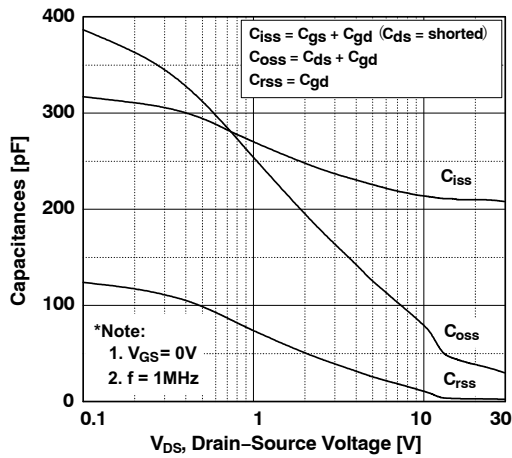


Figure 5. Capacitance Characteristics

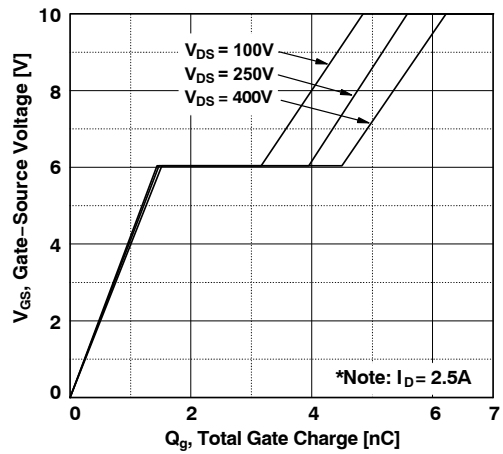


Figure 6. Gate Charge Characteristics

# FDU3N50NZTU

## TYPICAL CHARACTERISTICS

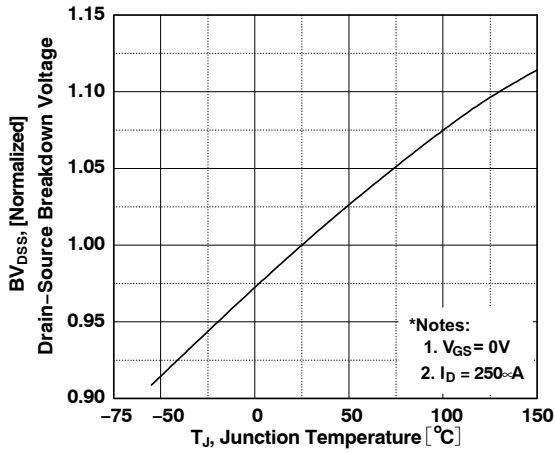


Figure 7. Breakdown Voltage Variation vs. Temperature

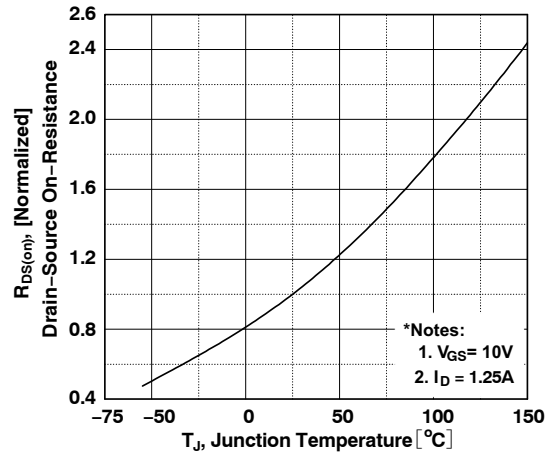


Figure 8. On-Resistance Variation vs. Temperature

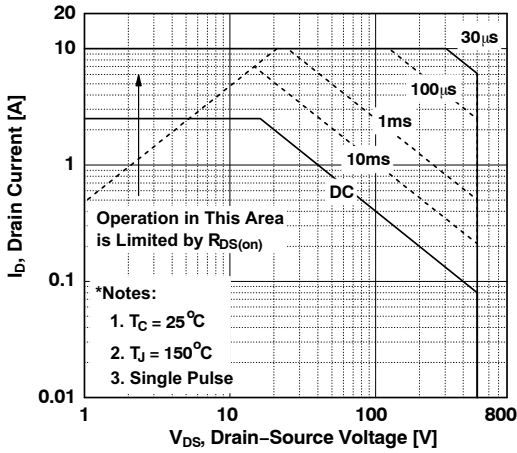


Figure 9. Maximum Safe Operating Area

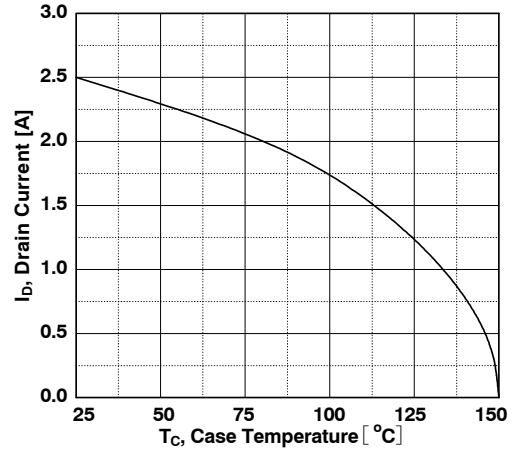


Figure 10. Maximum Drain Current vs. Case Temperature

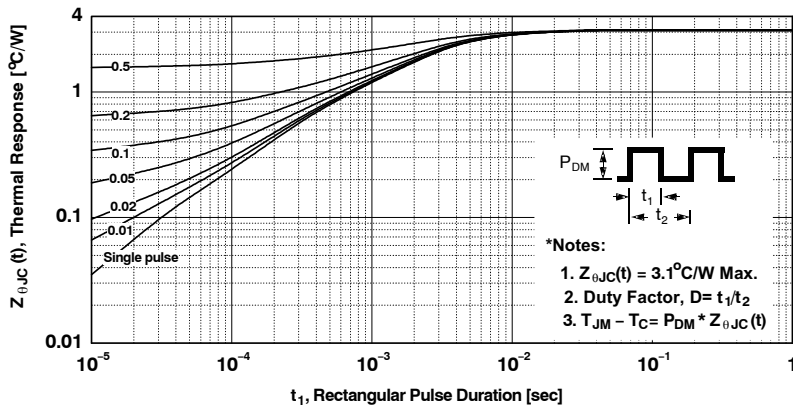


Figure 11. Transient Thermal Response Curve

# FDU3N50N2TU

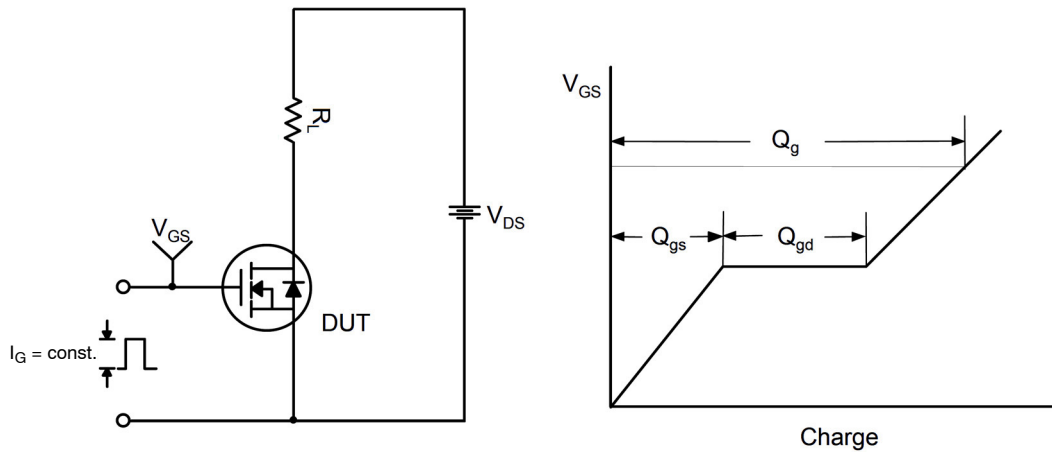


Figure 12. Gate Charge Test Circuit & Waveform

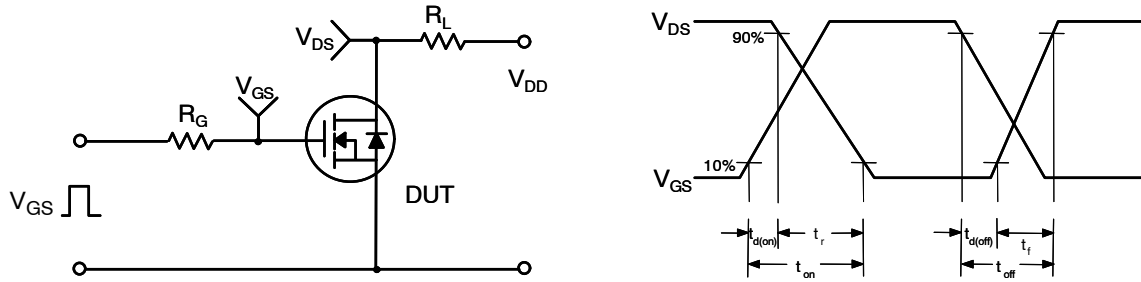


Figure 13. Resistive Switching Test Circuit & Waveforms

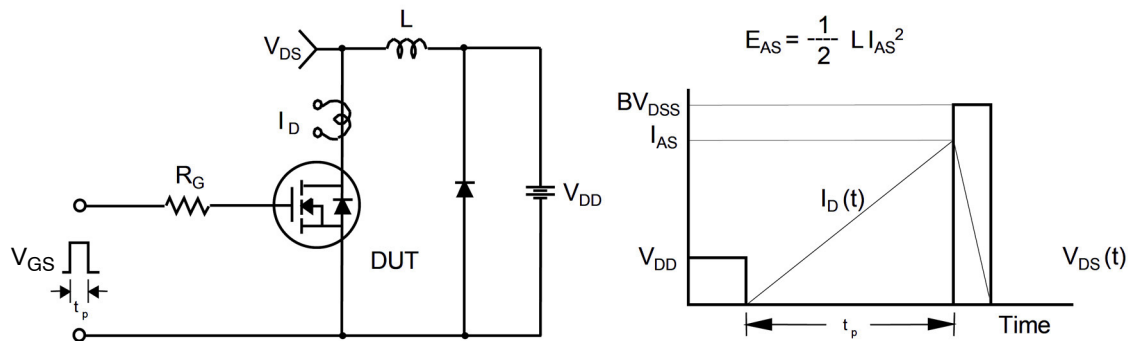


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

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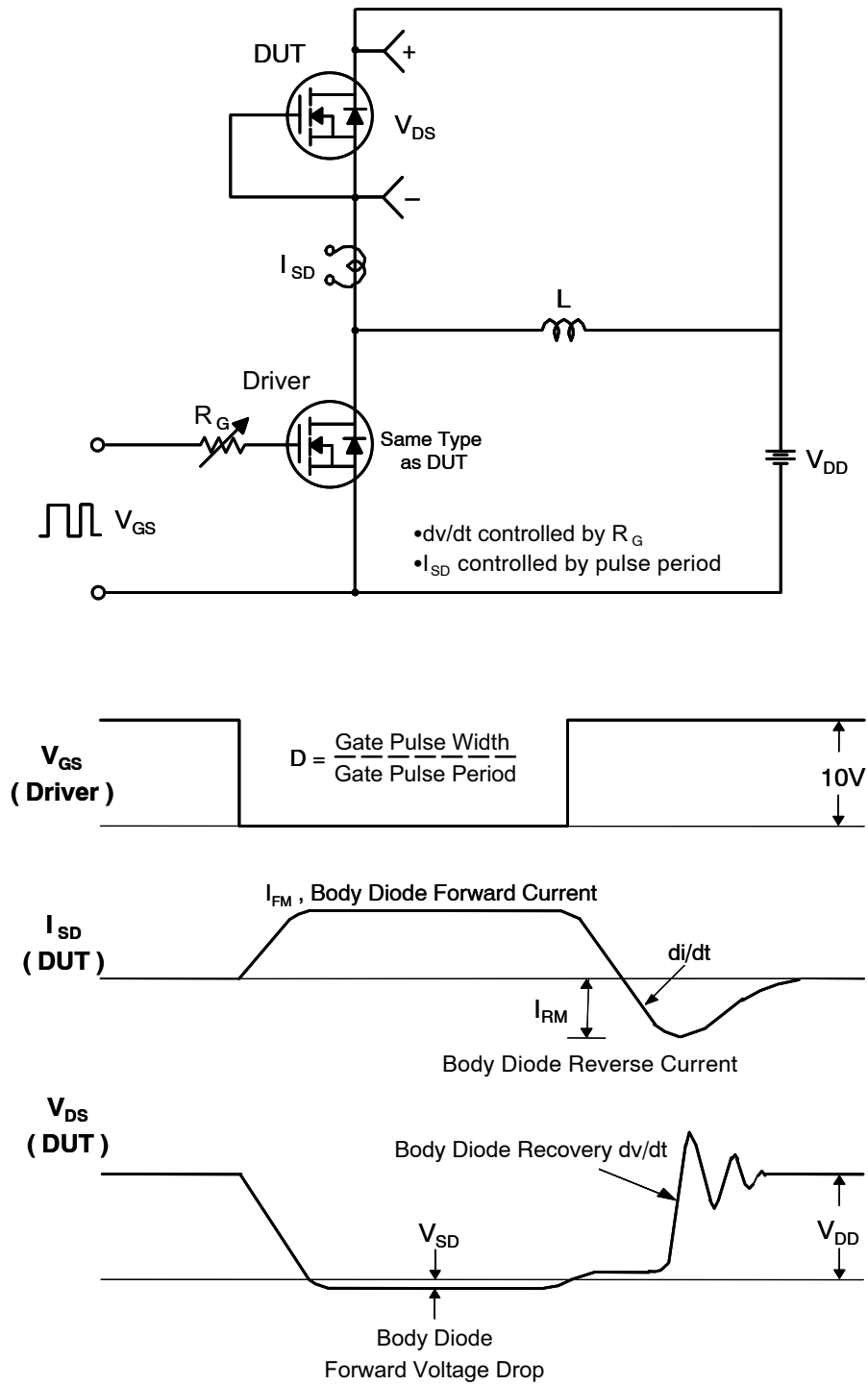


Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms

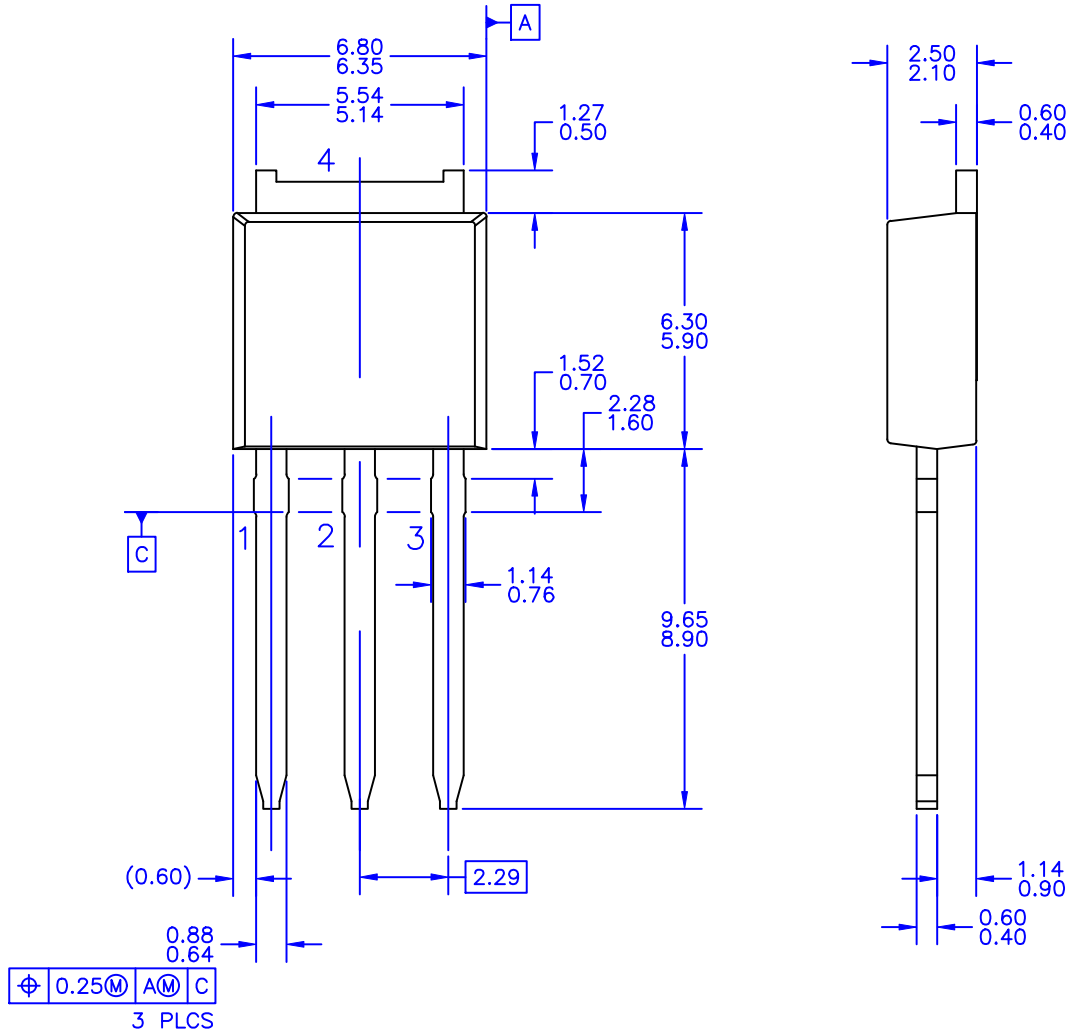
**MECHANICAL CASE OUTLINE**  
**PACKAGE DIMENSIONS**

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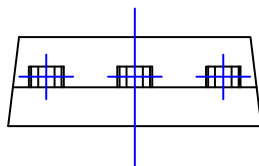
**DPAK3 (IPAK)**  
**CASE 369AR**  
**ISSUE O**

DATE 30 SEP 2016



NOTES: UNLESS OTHERWISE SPECIFIED

- A) ALL DIMENSIONS ARE IN MILLIMETERS.
- B) THIS PACKAGE CONFORMS TO JEDEC, TO-251, ISSUE C, VARIATION AA, DATED SEP 1988.
- C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.



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